

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor device can simply form a silicide film for reducing ohmic contact between a metal line and a substrate and a ternary phase thin film as an amorphous diffusion prevention film between a metal line and the silicide film. The method for manufacturing a semiconductor device includes the steps of sequentially forming a first refractory metal and a second refractory metal on a semiconductor substrate, forming a silicide film on an interface between the semiconductor substrate and the first refractory metal, and reacting the semiconductor substrate with the first and second refractory metals on the silicide film to form a ternary phase thin film.